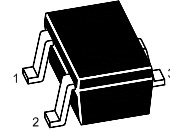
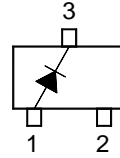


# 1SS370W

## Silicon Epitaxial Planar Diodes

High Voltage Switching Diode

For high voltage and high speed switching applications



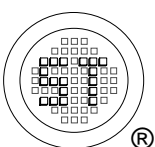
SOT-323 Plastic Package  
Marking Code: F5

### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	$V_{RM}$	250	V
Reverse Voltage	$V_R$	200	V
Average Rectified Forward Current	$I_{F(AV)}$	100	mA
Maximum Peak Forward Current	$I_{FM}$	300	mA
Non-repetitive Peak Forward Surge Current ( $t_p = 10\text{ ms}$ )	$I_{FSM}$	2	A
Power Dissipation	$P_D$	200	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 150	$^\circ\text{C}$

### Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 10\text{ mA}$ at $I_F = 100\text{ mA}$	$V_F$ $V_F$	1 1.2	V
Reverse Current at $V_R = 50\text{ V}$ at $V_R = 200\text{ V}$	$I_R$ $I_R$	0.1 1	$\mu\text{A}$
Total Capacitance at $V_R = 0, f = 1\text{ MHz}$	$C_T$	3	pF
Reverse Recovery Time at $I_F = 10\text{ mA}$	$t_{rr}$	60	ns

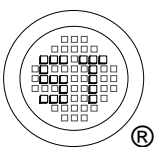
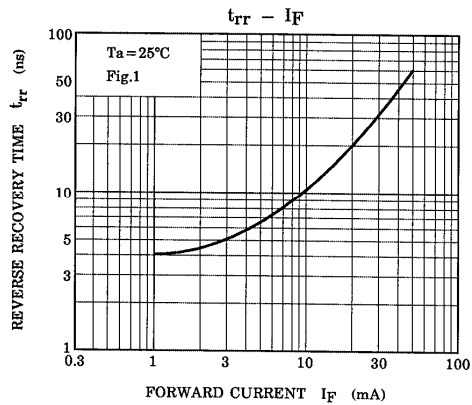
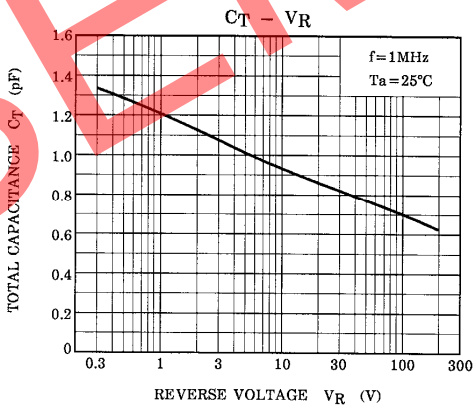
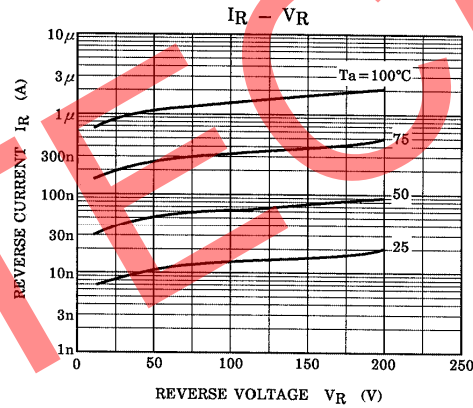
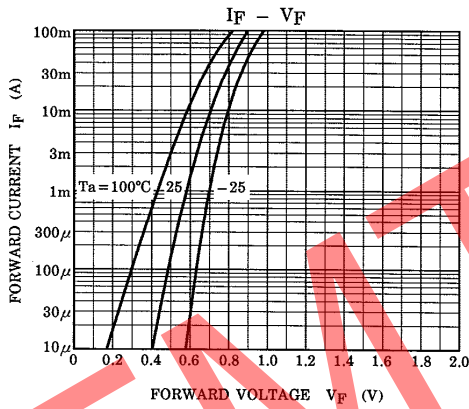
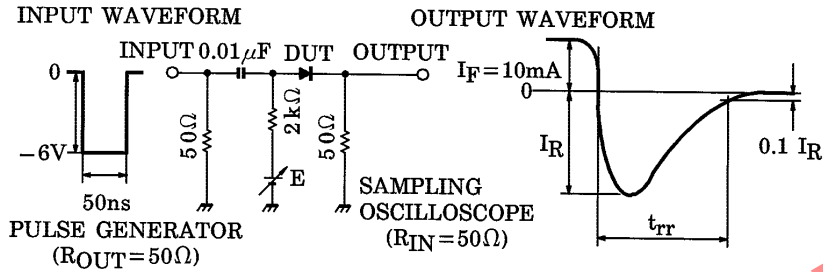


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Dated : 15/06/2009

Reverse Recovery Time ( $t_{rr}$ ) Test Circuit



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